

# HZM6.2Z4MWA

## Silicon Planar Zener Diode for Surge Absorb

REJ03G0368-0100 Rev.1.00 Oct 01, 2004

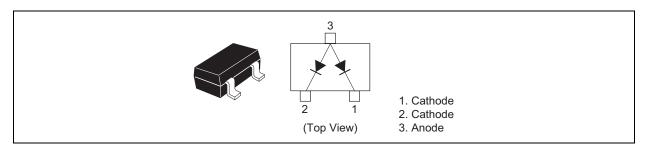
#### **Features**

- HZM6.2Z4MWA has two devices in a monolithic, and can absorb surge.
- Low capacitance (C = 4.0 pF Typ / 4.5 pF Max) and can protect ESD of signal line.
- MPAK Package is suitable for high density surface mounting and high speed assembly.

### **Ordering Information**

Type No.	Laser Mark	Package Code
HZM6.2Z4MWA	N1	MPAK

#### **Pin Arrangement**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol Value		Unit	
Power dissipation	Pd *	200	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	−55 to +150	°C	

Note: Two device total, See Fig.2.

## Electrical Characteristics \*1

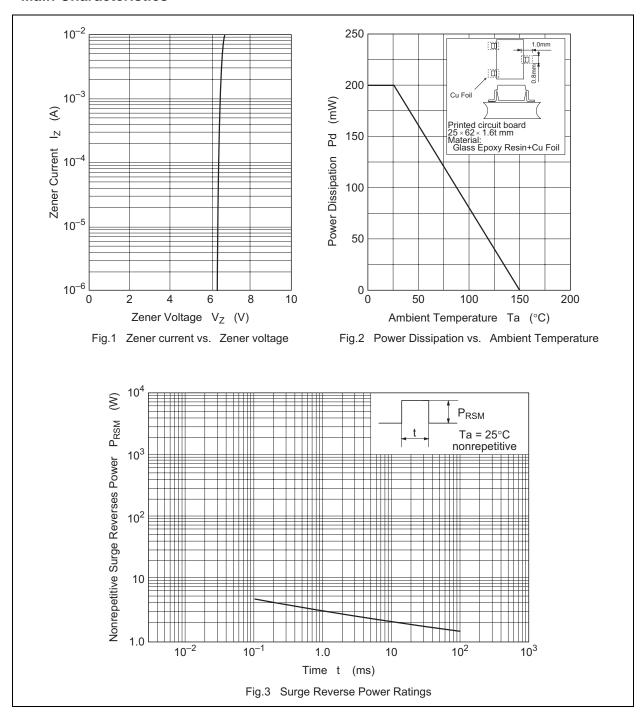
 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Zener voltage	V.z.	5.90	_	6.50	V	I <sub>Z</sub> = 5 mA, 40 ms pulse
Reverse current	I.R.	_	_	3	μΑ	V <sub>R</sub> = 5.5 V
Capacitance	С	_	4.0	4.5	pF	V <sub>.R</sub> . = 0 V, f = 1 MHz
Dynamic resistance	r <sub>d</sub> .	_	_	60	Ω	$I_Z = 5 \text{ mA}$
ESD-Capability *2	_	8	_	_	kV	$C = 150 \text{ pF}, R = 330 \Omega, Both forward}$
						and reverse direction 10 pulse

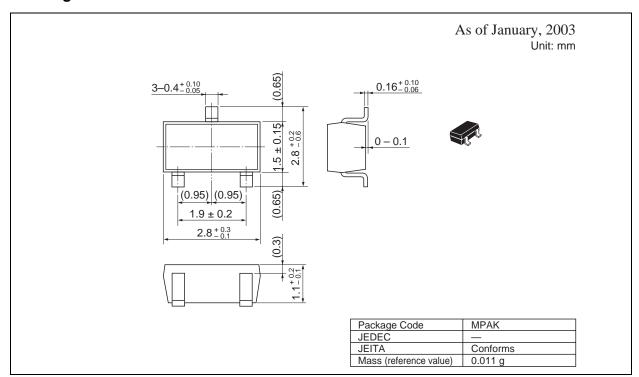
Notes: 1. Per one device.

2. Failure criterion ;  $I_{R} > 3~\mu A$  at  $V_{R} = 5.5~V.$ 

#### **Main Characteristics**



## **Package Dimensions**



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